**Product data sheet** 

## 1. General description

NPN low  $V_{CEsat}$  transistor in a SOT457 (SC-74) small Surface-Mounted Device (SMD) plastic package.

PNP complement: PBSS302PD

#### 2. Features and benefits

- Ultra low collector-emitter saturation voltage V<sub>CEsat</sub>
- 4 A continuous collector current capability I<sub>C</sub>
- Up to 15 A peak current
- · Very low collector-emitter saturation resistance
- · High efficiency due to less heat generation
- AEC-Q101 qualified

## 3. Applications

- Power management functions
- Charging circuits
- · DC-to-DC conversion
- MOSFET gate driving
- Power switches (e.g. motors, fans)
- Thin Film Transistor (TFT) backlight inverter

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-	40	V
Ic	collector current		[1]	-	-	4	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-	15	Α
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = 6 A; $I_B$ = 600 mA; pulsed; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C		-	55	75	mΩ

[1] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.



40 V, 4 A NPN low VCEsat transistor

## 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	С	collector		
2	С	collector	<u> </u>	C
3	В	base		В
4	Е	emitter	0 	. j
5	С	collector	TSOP6 (SOT457)	E sym123
6	С	collector		<i>5y</i> 25

# 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package		
	Name	Description	Version
PBSS302ND	TSOP6	plastic, surface-mounted package (SC-74; TSOP6); 6 leads	SOT457

## 7. Marking

### Table 4. Marking codes

Type number	Marking code
PBSS302ND	C7

# 8. Limiting values

### Table 5. Limiting values

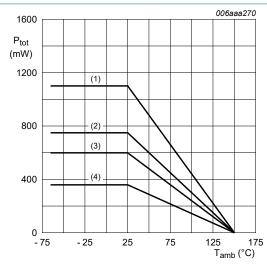
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	60	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	40	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	5	V
Ic	collector current		[1]	-	4	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	15	Α
I <sub>B</sub>	base current			-	0.8	Α
I <sub>BM</sub>	peak base current	single pulse; t <sub>p</sub> ≤ 1 ms		-	2	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[2]	-	360	mW
			[3]	-	600	mW
			[4]	-	750	mW
			[1]	-	1.1	W
			[2] [5]	-	2.5	W
T <sub>j</sub>	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-65	150	°C

#### 40 V, 4 A NPN low VCEsat transistor

Symbol	Parameter	Conditions	Min	Max	Unit
$T_{stg}$	storage temperature		-65	150	°C

- Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup> [3]
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>. [4]
- Operated under pulsed conditions: Duty cycle  $\delta \le 10$  % and pulse width  $t_p \le 10$  ms. [5]



- (1) Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm<sup>2</sup>
- (3) FR4 PCB, mounting pad for collector 1 cm<sup>2</sup>
- (4) FR4 PCB, standard footprint

Fig. 1. **Power derating curves** 

#### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$		[2] [3] [4]	[1]	-	-	350	K/W
	junction to ambient		[2]	-	-	208	K/W
			[3]	-	-	167	K/W
			-	-	113	K/W	
			[1] [5]	-	-	50	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	45	K/W

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>. [3]
- Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.
- Operated under pulsed conditions: Duty cycle  $\delta \le 10$  % and pulse width  $t_p \le 10$  ms.

PBSS302ND

#### 40 V, 4 A NPN low VCEsat transistor

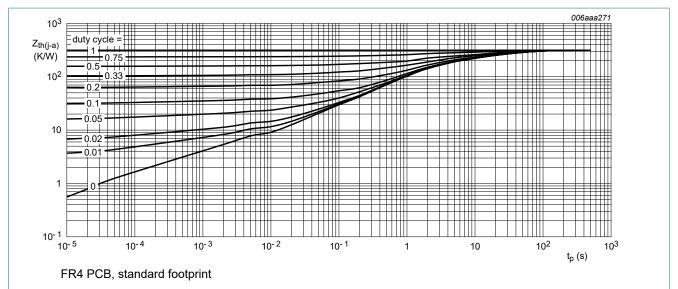


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

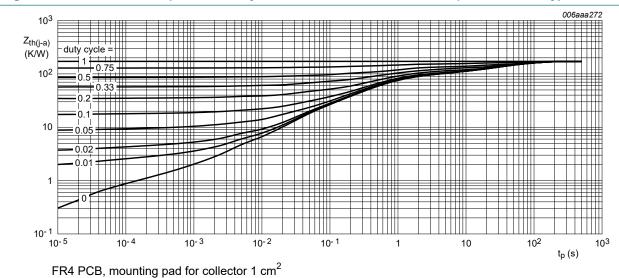


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

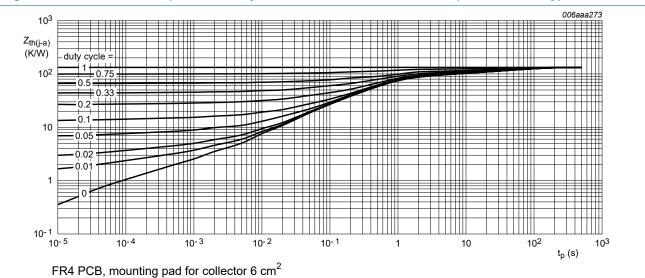


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

40 V, 4 A NPN low VCEsat transistor

## 10. Characteristics

#### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>СВО</sub>	collector-base cut-off	V <sub>CB</sub> = 40 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
	current	V <sub>CB</sub> = 40 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	50	μA
I <sub>ЕВО</sub>	emitter-base cut-off current	V <sub>EB</sub> = 5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
CES	collector-emitter cut-off current	V <sub>CE</sub> = 30 V; V <sub>BE</sub> = 0 V; T <sub>amb</sub> = 25 °C	-	-	100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 2 V; I <sub>C</sub> = 0.5 A; T <sub>amb</sub> = 25 °C	300	500	-	
		$V_{CE}$ = 2 V; $I_{C}$ = 1 A; pulsed; $t_{p} \le 300 \ \mu s$ ; δ ≤ 0.02; $T_{amb}$ = 25 °C	300	475	-	
		$V_{CE}$ = 2 V; $I_{C}$ = 2 A; pulsed; $t_{p}$ ≤ 300 μs; $\delta$ ≤ 0.02; $T_{amb}$ = 25 °C	250	385	-	
		$V_{CE}$ = 2 V; $I_{C}$ = 4 A; pulsed; $t_{p} \le 300 \ \mu s$ ; δ ≤ 0.02; $T_{amb}$ = 25 °C	100	190	-	
		$V_{CE}$ = 2 V; $I_{C}$ = 6 A; pulsed; $t_{p} \le 300 \ \mu s$ ; δ ≤ 0.02; $T_{amb}$ = 25 °C	50	100	-	
V <sub>CEsat</sub>	collector-emitter	$I_C = 0.5 \text{ A}; I_B = 50 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	-	35	60	mV
	saturation voltage	I <sub>C</sub> = 1 A; I <sub>B</sub> = 50 mA; T <sub>amb</sub> = 25 °C	-	65	110	mV
		I <sub>C</sub> = 2 A; I <sub>B</sub> = 200 mA; T <sub>amb</sub> = 25 °C	-	115	180	mV
		$I_C$ = 4 A; $I_B$ = 400 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	220	300	mV
		$I_C$ = 6 A; $I_B$ = 600 mA; pulsed; $t_p \le$	-	330	450	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	55	75	mΩ
V <sub>BEsat</sub>	base-emitter saturation	I <sub>C</sub> = 0.5 A; I <sub>B</sub> = 50 mA; T <sub>amb</sub> = 25 °C	-	0.79	0.85	V
	voltage	I <sub>C</sub> = 1 A; I <sub>B</sub> = 50 mA; T <sub>amb</sub> = 25 °C	-	0.81	0.9	V
		$I_C$ = 1 A; $I_B$ = 100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	0.83	1	V
		$I_C$ = 4 A; $I_B$ = 400 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	1	1.1	V
$V_{BEon}$	base-emitter turn-on voltage	V <sub>CE</sub> = 2 V; I <sub>C</sub> = 2 A; T <sub>amb</sub> = 25 °C	-	0.79	1	V
d	delay time	$V_{CC} = 10 \text{ V}; I_C = 2 \text{ A}; I_{Bon} = 0.1 \text{ A};$	-	12	-	ns
r	rise time	I <sub>Boff</sub> = -0.1 A; T <sub>amb</sub> = 25 °C	-	52	-	ns
on	turn-on time		-	64	-	ns
s	storage time		-	390	-	ns
-f	fall time		-	120	-	ns
off	turn-off time		-	510	-	ns
ŤΤ	transition frequency	$V_{CE}$ = 10 V; $I_{C}$ = 0.1 A; f = 100 MHz; $T_{amb}$ = 25 °C	-	150	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB}$ = 10 V; $I_{E}$ = 0 A; $i_{e}$ = 0 A; f = 1 MHz; $T_{amb}$ = 25 °C	-	30	-	pF

#### 40 V, 4 A NPN low VCEsat transistor

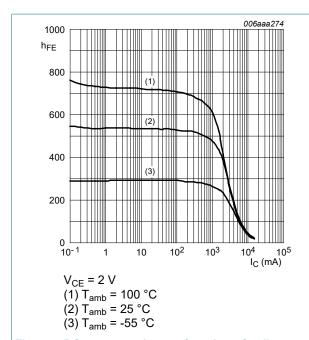


Fig. 5. DC current gain as a function of collector current; typical values

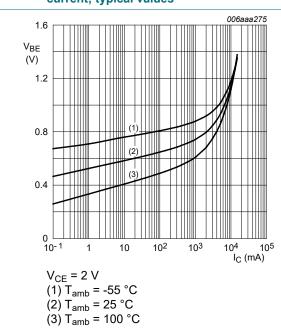


Fig. 7. Base-emitter voltage as a function of collector current; typical values

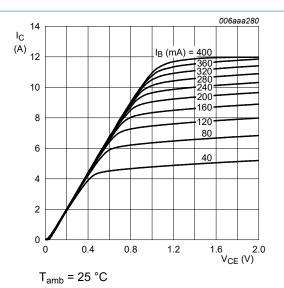
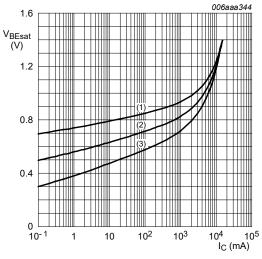


Fig. 6. Collector current as a function of collectoremitter voltage; typical values



 $I_{C}/I_{B} = 20$  (1)  $T_{amb} = -55 \,^{\circ}C$ 

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values

#### 40 V, 4 A NPN low VCEsat transistor

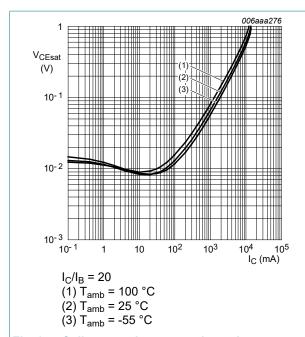


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

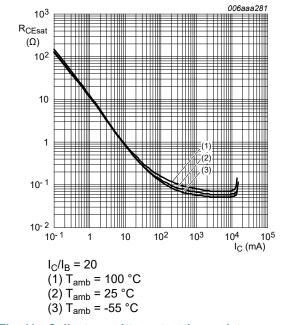


Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

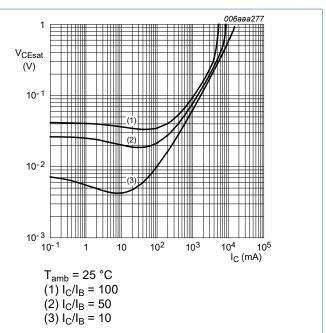
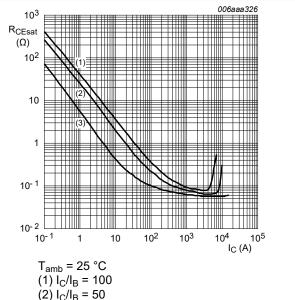


Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values

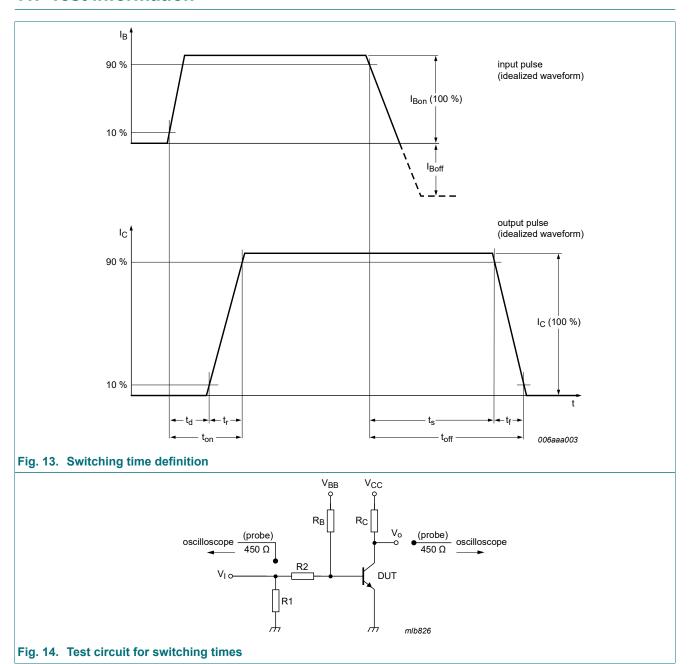


(2)  $I_{\rm C}/I_{\rm B} = 50$ (3)  $I_C/I_B = 10$ 

Fig. 12. Collector-emitter saturation resistance as a function of collector current; typical values

40 V, 4 A NPN low VCEsat transistor

## 11. Test information

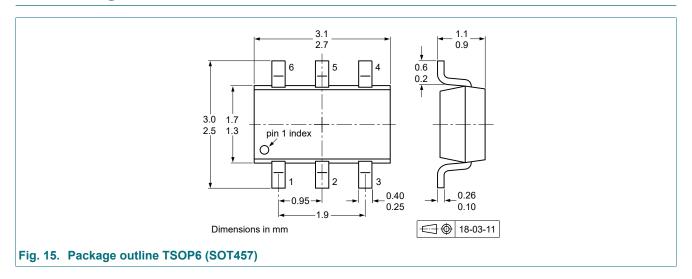


### **Quality information**

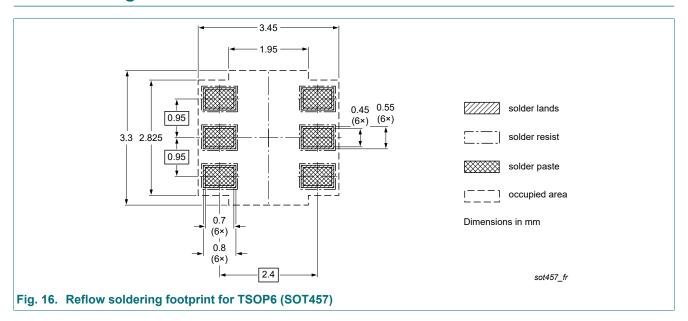
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

40 V, 4 A NPN low VCEsat transistor

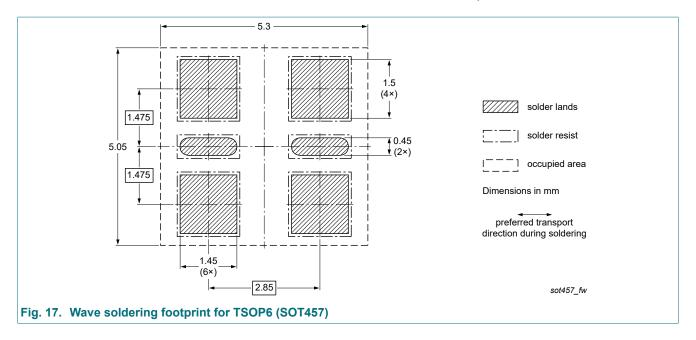
# 12. Package outline



## 13. Soldering



### 40 V, 4 A NPN low VCEsat transistor



40 V, 4 A NPN low VCEsat transistor

# 14. Revision history

#### **Table 8. Revision history**

D. C. J. L. CID	D. 1 1. (	B. G. Shandadada	01	0
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS302ND v.3	20230420	Product data sheet	-	PBSS302ND_2
Modifications:	Nexperia. • Legal texts have	this data sheet has been rede we been adapted to the new on ng information" removed.		
PBSS302ND_2	20080218	Product data sheet	-	PBSS302ND_1
PBSS302ND_1	20050419	Product data sheet	-	-

#### 40 V, 4 A NPN low VCEsat transistor

### 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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PBSS302ND

### 40 V, 4 A NPN low VCEsat transistor

## **Contents**

1.	General description	1
2.	Features and benefits	1
3.	Applications	1
4.	Quick reference data	1
5.	Pinning information	2
6.	Ordering information	2
7.	Marking	2
8.	Limiting values	2
9.	Thermal characteristics	3
10	. Characteristics	5
11.	. Test information	8
12	. Package outline	9
	. Soldering	
	. Revision history	
	. Legal information	

For more information, please visit: http://www.nexperia.com For sales office addresses, please send an email to: salesaddresses@nexperia.com Date of release: 20 April 2023

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